

## 700V 7A N-Channel Enhancement Mode Power MOSFET

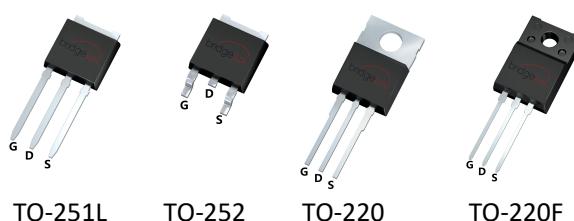
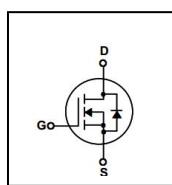
### General Description

BXP7N70 is Bridgelux high voltage MOSFET family based on advanced planar stripe DMOS technology. This advanced MOSFET family has optimized on-state resistance, and also provides superior switching performance and higher avalanche energy strength. This device family is suitable for high efficiency switch mode power supplies.

### FEATURES

- $R_{DS(on)} \leq 1.5 \Omega$  @  $V_{GS} = 10V$ ,  $I_D = 3.5A$
- Excellent  $R_{DS(on)}$  and Low Gate Charge
- Fast switching capability
- Lead free product is acquired

### SYMBOL



### ASSEMBLY MESSAGE

Product Name	Marking	Package	Packaging
BXP7N70U	BXP7N70U	TO-251L	Tube
BXP7N70D	BXP7N70D	TO-252	Tube/Reel
BXP7N70P	BXP7N70P	TO-220	Tube
BXP7N70F	BXP7N70F	TO-220F	Tube

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Rating			Unit
		BXP7N70U/D	BXP7N70P	BXP7N70F	
Drain-Source Voltage	$V_{DSS}$	700			V
Drain Current	$I_D$	7			A
		4.1			A
Drain Current	$I_{DM}$	28			A
Gate-Source Voltage	$V_{GSS}$	$\pm 30$			V
Avalanche Energy	Single Pulse (Note2)	441			mJ
	Repetitive (Note1)	21			mJ
Avalanche Current (Note1)	$I_{AR}$	7			A
Peak Diode Recovery $dv/dt$ (Note3)	$dv/dt$	5			V/ns
Power Dissipation (Note 2)	$P_D$	114	130	38	W
		0.912	1.04	0.304	$W/\text{ }^\circ C$
Maximum Junction Temperature	$T_J$	150			$^\circ C$
Storage Temperature Range	$T_{STG}$	-55 to 150			$^\circ C$

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature

2.  $L=18\text{mH}$ ,  $V_{DD}=50\text{V}$ ,  $R_G=25\Omega$ , Starting  $T_J = 25^\circ C$

3.  $I_{SD} \leq 7.0\text{A}$ ,  $di/dt \leq 100\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ C$

**THERMAL CHARACTERISTICS**

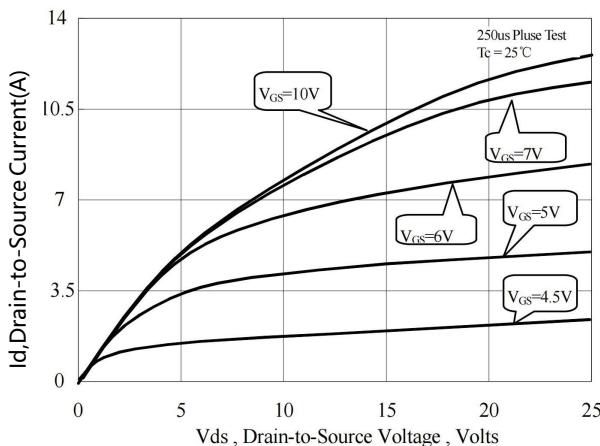
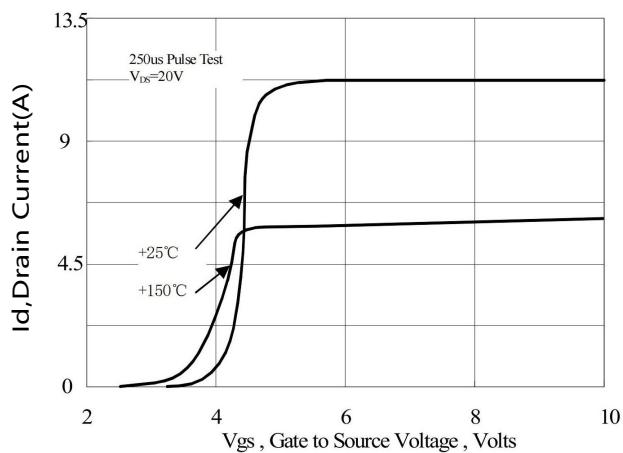
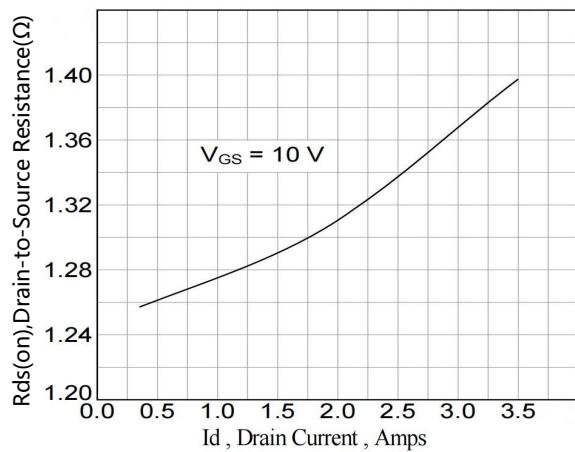
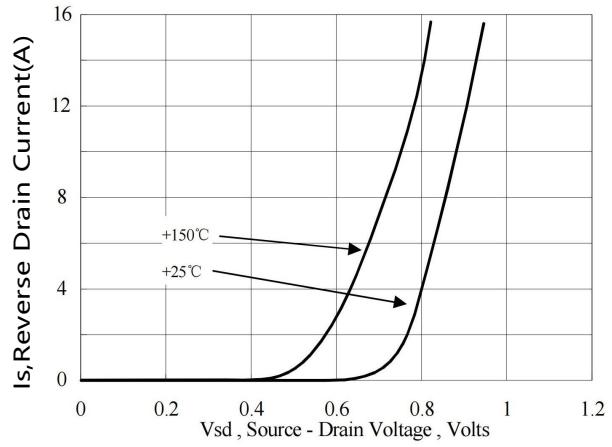
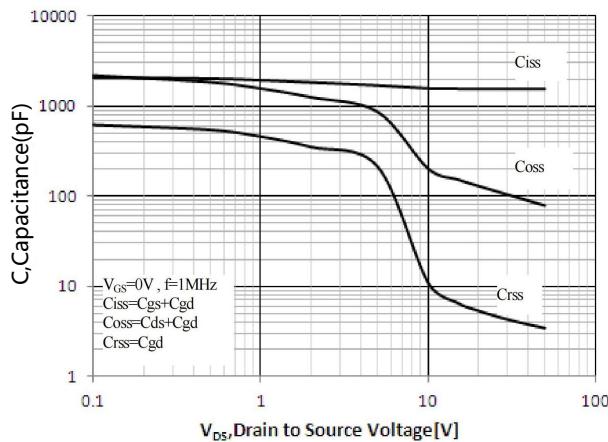
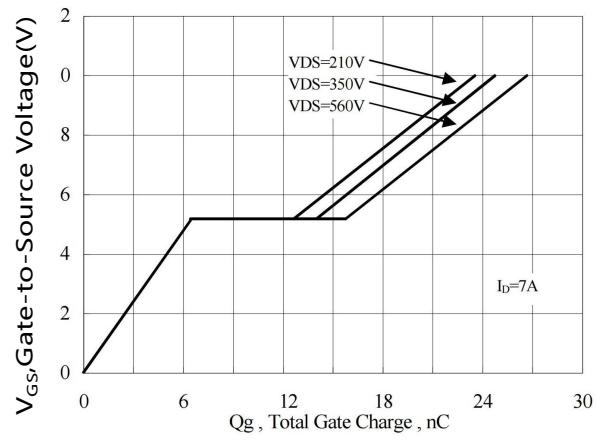
Parameter	Symbol	Max.			Unit
		BXP7N70U/D	BXP7N70P	BXP7N70F	
Thermal Resistance, Junction-to-Case	R <sub>θJC</sub>	1.1	0.96	3.3	°C / W
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub>	62.5	62.5	120	°C / W

**ELECTRICAL CHARACTERISTICS** (T<sub>J</sub>=25°C,unless otherwise Noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, ID=250μA	700			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =700V, V <sub>GS</sub> =0V			1	uA
		V <sub>DS</sub> =560V, TC = 125°C			100	uA
Gate-Body Leakage Current, Forward	I <sub>GSS</sub>	V <sub>GS</sub> =30V			100	nA
Gate-Body Leakage Current, Reverse		V <sub>GS</sub> =-30V			-100	nA
Breakdown Voltage Temperature Coefficient	△BV <sub>DSS</sub> /△T <sub>J</sub>	ID = 250 μA		0.72		V/°C
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , ID=250μA	2		4	V
Drain-Source On-State Resistance	R <sub>D(S)</sub>	V <sub>GS</sub> =10V, ID=3.5A		1.35	1.5	Ω
Forward Transconductance (Note4)	g <sub>FS</sub>	V <sub>DS</sub> = 50V, ID = 3.5A		7.5		S
<b>DYNAMIC PARAMETERS</b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHz		1610		pF
Output Capacitance	C <sub>OSS</sub>			110		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			4.5		pF
<b>SWITCHING PARAMETERS</b>						
Turn-ON Delay Time	t <sub>D(ON)</sub>	VDD=350V, ID=7 A, VGS = 10V ,RG=10Ω (Note4,5)		24		ns
Turn-ON Rise Time	t <sub>R</sub>			16		ns
Turn-OFF Delay Time	t <sub>D(OFF)</sub>			40		ns
Turn-OFF Fall-Time	t <sub>F</sub>			15		ns
Total Gate Charge(Note5)	Q <sub>G</sub>	VDS =560V, VGS =10V, ID =7A (Note4,5)		25		nC
Gate Source Charge	Q <sub>GS</sub>			6.1		nC
Gate Drain Charge	Q <sub>GD</sub>			9		nC
<b>SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS</b>						
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =7A, V <sub>GS</sub> =0V			1.4	V
Diode Continuous Forward Current	I <sub>S</sub>				7	A
Pulsed Drain-Source Current	I <sub>SM</sub>				28	A
Reverse Recovery Time	t <sub>RR</sub>	V <sub>GS</sub> = 0 V, ISD = 7A di/dt=100 A/μs (Note4,5)		320		ns
Reverse Recovery Charge	Q <sub>RR</sub>			2.7		uC

Note: 4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%

5. Essentially independent of operating temperature

**TYPICAL CHARACTERISTICS****Figure1. Typical Output Characteristics****Figure2. Typical Transfer Characteristics****Figure3. On-Resistance versus Drain Current****Figure4. Diode forward voltage versus Current****Figure5. Typical Capacitance versus  $V_{ds}$** **Figure6. Typical Gate Charge versus  $V_{gs}$**

## TYPICAL CHARACTERISTICS(Cont.)

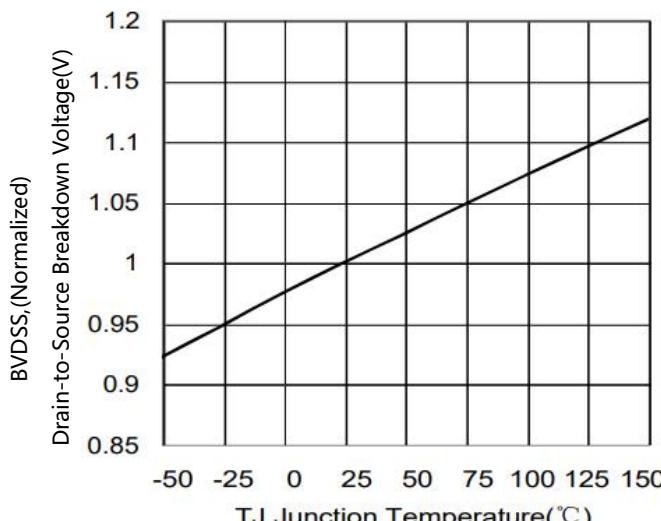
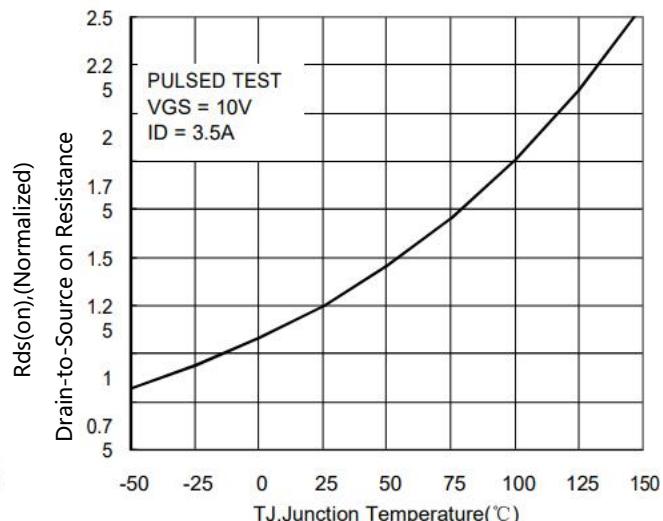
Figure 7.  $BV_{DSs}$  Variation with Temperature

Figure 8. On-Resistance Variation with Temperature

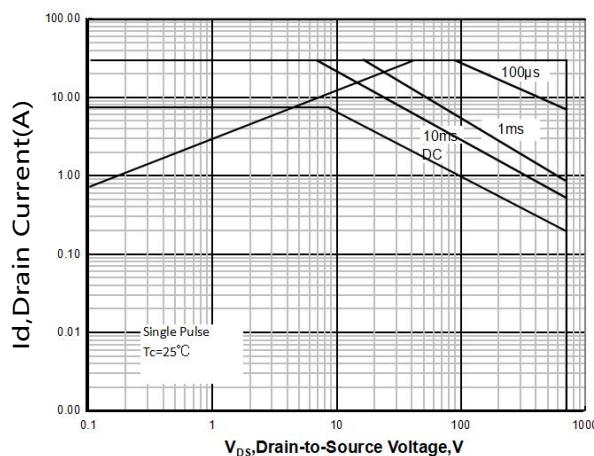


Figure 9. Maximum Safe Operating Area

BXP7N70U/D/P

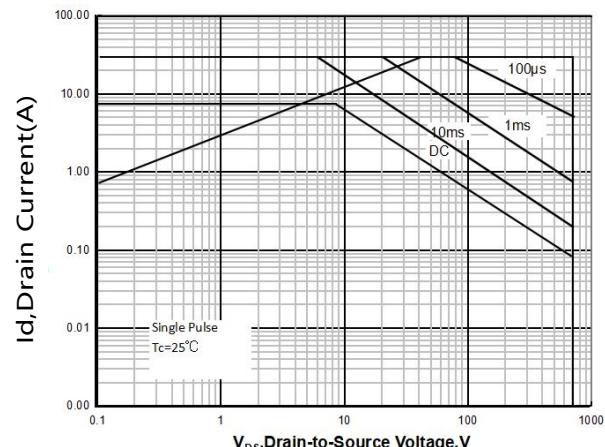


Figure 9. Maximum Safe Operating Area

BXP7N70F

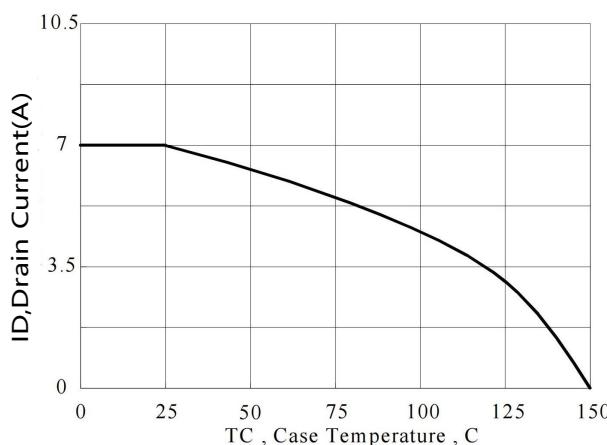
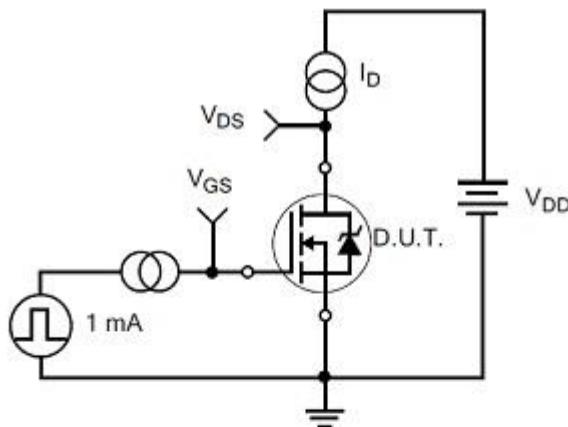
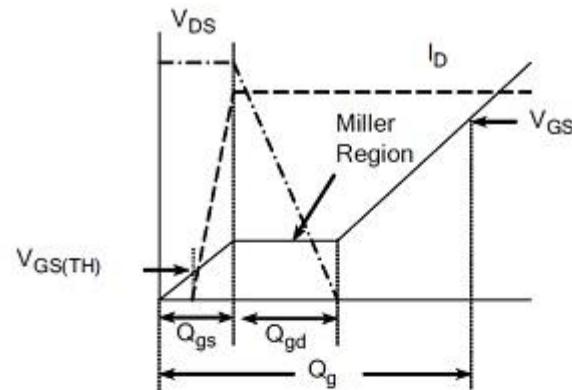


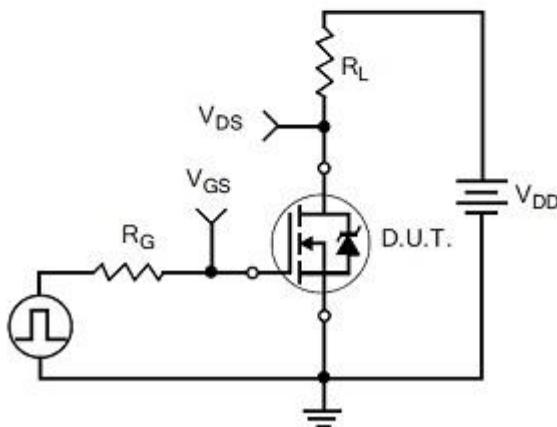
Figure 10. Maximum Continuous Drain Current versus Case Temperature

**TEST CIRCUITS AND WAVEFORMS**

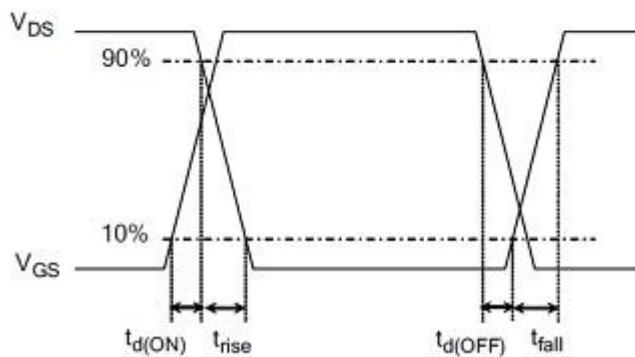
Gate Charge Test Circuit



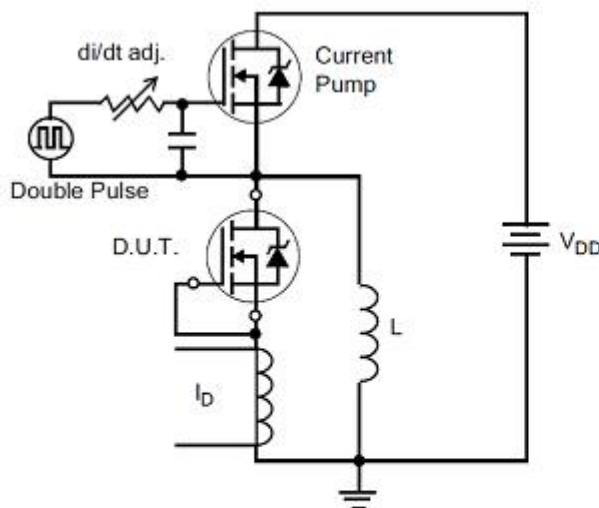
Gate Charge Waveform



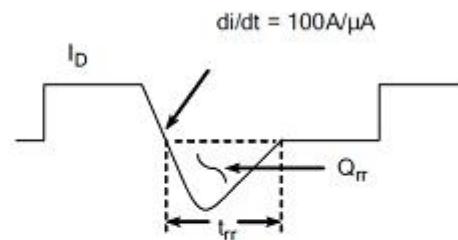
Resistive Switching Test Circuit



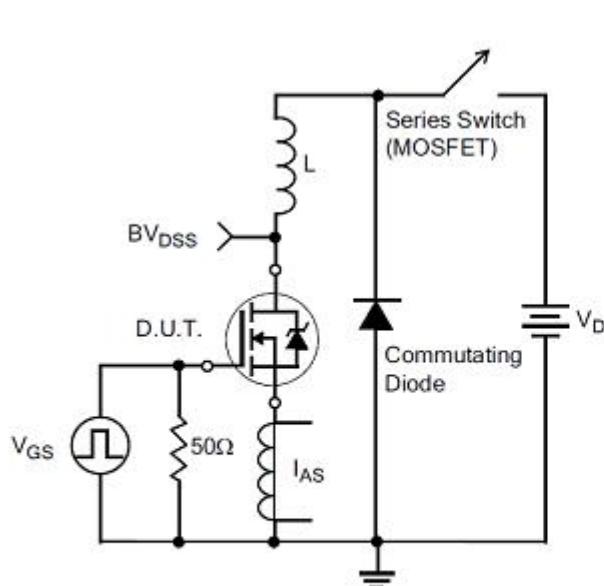
Resistive Switching Waveforms

**TEST CIRCUITS AND WAVEFORMS(Cont.)**

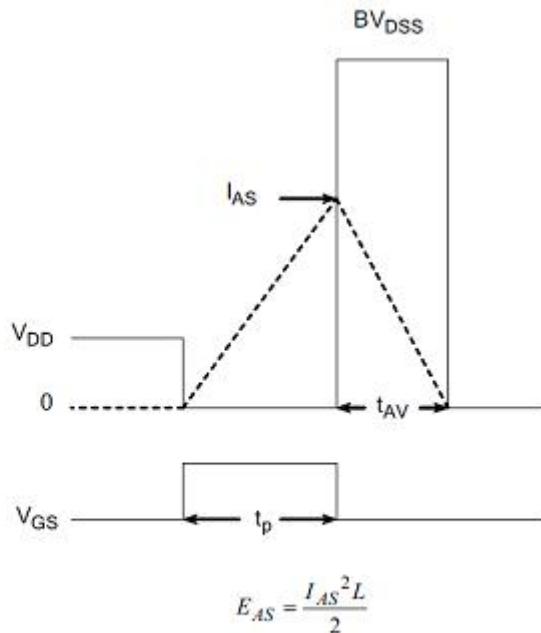
Diode Reverse Recovery Test Circuit



Diode Reverse Recovery Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

## Revision history

### Document revision history

Date	Revision	Changes
12-Oct-2021	1.0	First release
5-Jan-2022	1.1	Update parameter

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